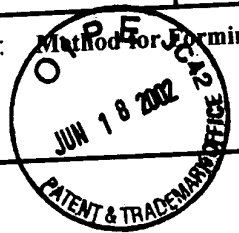


2829

<b>AMENDMENT TRANSMITTAL LETTER (Large Entity)</b>			Docket No. SLA0592
Applicant(s): Apostolos Voutsas			
Serial No. 09/893,866	Filing Date 06/28/2001	Examiner Asok K. Sarkar	Group Art Unit 2829

Inv ntion: Method for Forming Silicon Films with Trace Impurities  
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TO THE ASSISTANT COMMISSIONER FOR PATENTS:

Transmitted herewith is an amendment in the above-identified application.  
The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED					
	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST # PREV. PAID FOR	NUMBER EXTRA CLAIMS PRESENT	RATE	ADDITIONAL FEE
TOTAL CLAIMS	23 -	23 =	0 x	\$18.00	\$0.00
INDEP. CLAIMS	2 -	3 =	0 x	\$84.00	\$0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					\$0.00
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0.00

- ☐ No additional fee is required for amendment.
- ☐ Please charge Deposit Account No. \_\_\_\_\_ in the amount of \_\_\_\_\_
- ☐ A duplicate copy of this sheet is enclosed.
- ☐ A check in the amount of \_\_\_\_\_ to cover the filing fee is enclosed.
- ☒ The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 19-1457  
A duplicate copy of this sheet is enclosed.
- ☒ Any additional filing fees required under 37 C.F.R. 1.16.
- ☒ Any patent application processing fees under 37 CFR 1.17.

Signature

Dated: June 13, 2002

David C. Ripma, Patent Counsel  
Sharp Laboratories of America, Inc.  
5750 NW Pacific Rim Boulevard  
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Phone: 360-834-8754  
Facsimile: 360-817-8505

I certify that this document and fee is being deposited on June 13, 2002 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.
 Signature of Person Mailing Correspondence
David C. Ripma, Reg. No. 27,672
Typed or Printed Name of Person Mailing Correspondence

CC:

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#5/A  
7/12/02  
Hayes

In Re Application of:

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Inventors: Apostolos Voutsas

Serial No.: 09/893,866

Filed: June 28, 2001

Title: METHOD FOR FORMING  
SILICON FILMS WITH TRACE  
IMPURITIES

ATTORNEY FILE NO.  
SLA592

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**CERTIFICATION UNDER 37 CFR § 1.8**

I hereby certify that the documents referred to as enclosed herein are being deposited with the United States Postal Service as first class mail on this date June 13, 2002 in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231

Date

8/13/02

Signature

David C. Ripma  
Reg. No. 27,672

BOX NO FEE AMEND

Assistant Commissioner for Patents  
Washington, D.C. 20231

**AMENDMENT AND REQUEST FOR RECONSIDERATION**

In response to an Office Action filed April 17, 2002, please accept the following amendments and reconsider.

**IN THE SPECIFICATION:**

On page 3, please delete the three paragraphs from lines 10 through 26, and substitute therefor the following three paragraphs.

A'  
Forming a target including silicon and a first concentration of a first impurity includes using a first impurity selected from the group including transition metals, phosphorous, and germanium. When the first impurity is Ni, the first concentration of nickel in the target is in the range of 0.01 to 0.5 atomic percent (at %). Preferably the range is 0.05 to 0.2 at %. Then, the second